



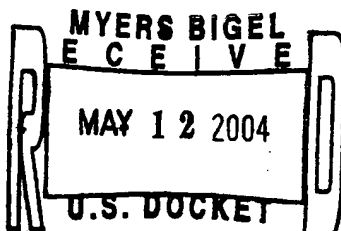
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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/780,245	02/18/2004	2812	770	5649-1200	7	15	1

20792
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CONFIRMATION NO. 9654

FILING RECEIPT



OC000000012574829

Date Mailed: 05/10/2004

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Domestic Priority data as claimed by applicant

Foreign Applications

REPUBLIC OF KOREA 10-2003-10323 02/19/2003

If Required, Foreign Filing License Granted: 05/07/2004

Projected Publication Date: To Be Determined - pending completion of Missing Parts

Non-Publication Request: No

Early Publication Request: No

05-12-04 A09:13 IN

Title

Methods of fabricating MOS field effect transistors with pocket regions